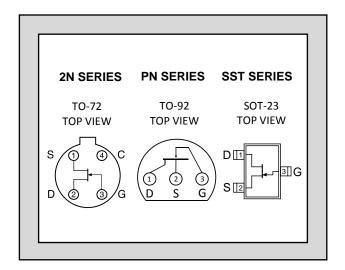


Twenty-Five Years Of Quality Through Innovation

2N/PN/SST 4117, 4118, 4119

ULTRA-HIGH INPUT IMPEDANCE N-CHANNEL JFET AMPLIFIER

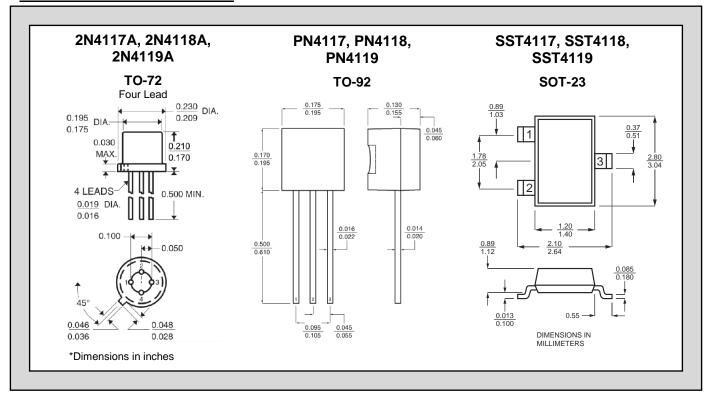
FEATURES								
LOW POWER	(2N4117A)							
MINIMUM CIRCUIT LOADING	2N4117A Series)							
ABSOLUTE MAXIMUM RATINGS (NOTE 3)								
@ 25°C (unless otherwise noted)								
Gate-Source or Gate-Drain Volta	-40V							
Gate-Current	50mA							
Total Device Dissipation								
(Derate 2mW/°C above 25°C)	300mW							
Storage Temperature Range	-55°C to+150°C							
Lead Temperature								
(1/16" from case for 10 seconds)	300°C							



ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

		4117		4118		4119				
SYMBOL	CHARACTERISTIC	MIN	MAX	MIN	MAX	MIN	MAX	UNITS	CONDITIONS	
BV _{GSS}	Gate-Source Breakdown Voltage	-40		-40	1	-40	ı	V	I _G =-1μA V _{DS} =0	
V _{GS(off)}	Gate-Source Cutoff Voltage	-0.6	-1.8	-1	-3	-2	-6		V _{DS} =10V I _D =1nA	
I _{DSS}	Saturation Drain Current (NOTE 2)	0.03	0.60	0.08	0.60	0.20	0.80	mA	V _{DS} =10V V _{GS} =0	
Igss	Gate Reverse Current 2N4117A, 2N4118A, 2N4119A		-1		-1		-1	pA nA	V _{GS} =-20V V _{DS} =0	
			-2.5		-2.5		-2.5			150°C
	PN4117, PN4118, PN4119 SST4117, SST4118, SST4119		-10		-10		-10	pА	V _{GS} =-10V V _{DS} =0	
		1	-25	1	-25	1	-25	nA	VGS =-10V VDS=0	150°C
G fs	Common-Source Forward Transconductance	70	450	80	650	100	700	μS pF	V _{DS} =10V V _{GS} =0	f=1kHz
gos	Common-Source Output Conductance		3		5		10			I=INIIZ
Ciss	Common-Source Input Capacitance (NOTE 4)		3		3		3			f=1MHz
Crss	Common-Source Reverse Transfer Capacitance (NOTE 4)	-	1.5	-	1.5	-	1.5			ı≓ııvı⊓Z

STANDARD PACKAGE DIMENSIONS:



NOTES:

- 1. Due to symmetrical geometry, these units may be operated with source and drain leads interchanged.
- 2. This parameter is measured during a 2 ms interval 100 ms after power is applied. (Not a JEDEC condition.)
- 3. Absolute maximum ratings are limiting values above which serviceability may be impaired.
- 4. Not production tested, guaranteed by design.

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Linear Integrated Systems (LIS) is a 25-year-old, third-generation precision semiconductor company providing high-quality discrete components. Expertise brought to LIS is based on processes and products developed at Amelco, Union Carbide, Intersil and Micro Power Systems by company President John H. Hall. Hall, a protégé of Silicon Valley legend Dr. Jean Hoerni, was the director of IC Development at Union Carbide, Co-Founder and Vice President of R&D at Intersil, and Founder/President of Micro Power Systems.